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**MCDERMOTT, WILL & EMERY****FACSIMILE****FROM:**

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Secretary:	<u>Connie Collins</u>	Direct Phone:	<u>202-756-8659</u>
Client/Matter/Tkpr:	<u>57454-062</u>	Date:	<u>11/4/02</u> Time Sent: <u>          </u>
		Number of pages including this page:	<u>-17-</u>

**TO:**

Name:	<u>Examiner Johannes Mondt</u>	Facsimile No.	<u>703-746-5176</u>
Company:	<u>U.S. Patent &amp; Trademark Office</u>	Contact No.	<u>703-306-0531</u>

**MESSAGE:** Per our telephone conference, attached is the timely filing of Sept 4, 2002.

**PLEASE CONFIRM RECEIPT OF THIS FAX BY PHONING  
CONSTANCE COLLINS AT THE ABOVE NUMBER. THANK-YOU**

The information contained in this facsimile message is legally privileged and confidential information intended only for the use of the individual or entity named above. If the reader of this message is not the intended recipient, you are hereby notified that any dissemination, distribution, or copy of this facsimile is strictly prohibited. If you have received this facsimile in error, please notify us immediately by telephone and return the original message to us at the above address via the United States Postal Service. Thank you.

WDC99 453298-11.049657.0677

FAX RECEIVED

NOV 4 2002

T.C. 2800

Applicant: Tomohide TERASHIMA Docket No. 57454-062

Title: SEMICONDUCTOR DEVICE Serial/Reg./Patent No. 09/834,954

Date Sent: 9/4/2002 ☒ Hand Carried ☐ Fax ☐ Electronic ☐ Cert. of Mailing ☐ Express Mail No. \_\_\_\_\_

☒ Transmittal Letter ☐ Utility ☐ Design ☐ Cont. ☐ CIP ☐ Div. ☐ PCT ☐ CPA ☐ RCE ☐ Prov

☐ New Patent App. ☐ Other: \_\_\_\_\_

☐ Other: \_\_\_\_\_

☐ pages of Specification

☐ pages of Claims

☐ pages of Abstract

☐ pages of Formal/Informal Drawings

☐ Small Entity ☐ Large Entity

☐ Declaration/Power of Attorney

☐ Recordation of Assignment/Security Agreement

☐ Information Disclosure Statement

☐ Form PTO 1449

☐ copies of cited references

☐ Preliminary Amendment

☐ Response to Missing Parts Notice

☐ Resp. to Notice to Correct App. Papers

☐ Certified Copy of Priority Doc.

☐ Claim for Convention Priority

☒ Response/Amendment to Office Action of 6/4/02

☐ Request for month Extension of Time

Check for \$ ☐ Charge Deposit Acc. 500417 \$ -0- Any Init. SDP Tqtr. # 5605 Secy. or P.L. CA, Collins

CMS Descrip.: \_\_\_\_\_

THE PATENT AND TRADEMARK OFFICE DATE STAMPED HEREON IS ACKNOWLEDGEMENT THAT THE ITEMS CHECKED ABOVE WERE RECEIVED BY THE PTO ON THE DATE STAMPED.



- ☐ Letter submitting \_\_\_\_\_ pages of drawings
- ☐ Req. for Approval of Drawing Amendments
- ☐ Req. for Oral Hearing
- ☐ Not. of Appeal ☐ Appeal Brief ☐ Reply Brief
- ☐ Rule 312 Amendment/Letter
- ☐ Req. for Acknowledgement of Cited Art
- ☐ Issue Fee
- ☐ Publication Fee
- ☐ Req. for Certificate of Correction
- ☐ Maintenance Fee for \_\_\_\_\_ years after grant
- ☐ Fee Address Indication Form
- ☐ Terminal Disclaimer
- ☐ Petition to Commissioner
- ☐ Status Inquiry
- ☐ Other

Docket #: 57454-062

**PATENT**

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of : **RESPONSE UNDER 37 CFR 1.116**  
 : **- EXPEDITED PROCEDURE**  
 Tomohide TERASHIMA :  
 :  
 Serial No.: 09/834,954 : Group Art Unit: 2826  
 :  
 Filed: April 16, 2001 : Examiner: Johannes P. Mondt  
 :  
 For: SEMICONDUCTORDEVICE

**BOX AF**  
 THE COMMISSIONER FOR PATENTS AND TRADEMARKS  
 Washington, DC 20231

Dear Sir:

Transmitted herewith is an Amendment in the above identified application.

- ☒ No additional fee is required.  
☐ Applicant is entitled to small entity status under 37 CFR 1.27  
☐ Also attached:

The fee has been calculated as shown below:

	NO. OF CLAIMS	HIGHEST PREVIOUSLY PAID FOR	EXTRA CLAIMS	RATE	FEE
Total Claims	12	20	0	\$18.00 =	\$0.00
Independent Claims	2	3	0	\$84.00 =	\$0.00
Multiple claims newly presented					\$0.00
Fee for extension of time					\$0.00
Total of Above Calculations					\$0.00

- ☐ Please charge my Deposit Account No. 500417 in the amount of \$0.00. An additional copy of this transmittal sheet is submitted herewith.
- ☒ The Commissioner is hereby authorized to charge payment of any fees associated with this communication or credit any overpayment, to Deposit Account No. 500417, including any filing fees under 37 CFR 1.16 for presentation of extra claims and any patent application processing fees under 37 CFR 1.17.

Respectfully submitted,

MCDERMOTT, WILL &amp; EMERY



Scott D. Paul  
 Registration No. 42,984

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N.B. Please enter at this time. Thank you. *[Signature]*  
Please: Do Not enter. *[Signature]*  
(12/18/02) (3/4/3)

Docket No.: 57454-062

PATENT

#8  
Amend  
B  
(NE)  
12/17/02  
*[Signature]*

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

: RESPONSE UNDER 37 CFR 1.116

Tomohide TERASHIMA

: EXPEDITED PROCEDURE

Application No.: 09/834,954

: Group Art Unit: 2826

Filed: April 16, 2001

: Examiner: J. Mondt

For: SEMICONDUCTOR DEVICE

AMENDMENT UNDER 37 C.F.R. § 1.116

BOX AF

The Commissioner for Patents and Trademarks  
Washington, DC 20231

Sir:

The following Amendment and Remarks are submitted in response to the Final Office Action dated June 4, 2002, pursuant to the provisions of 37 C.F.R. § 1.116. Please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 1 and 10 as follows:

- B/
1. (Amended) A semiconductor device including:  
a semiconductor substrate having a main surface;  
a semiconductor layer of a first conductive type which is formed on the main surface of said semiconductor substrate;  
a first buried impurity region of the first conductive type formed between said semiconductor layer and said semiconductor substrate;